

Title (en)

METHOD FOR THE PRODUCTION OF TRENCH CAPACITORS FOR INTEGRATED SEMICONDUCTOR MEMORIES

Title (de)

VERFAHREN ZUR HERSTELLUNG VON GRABENKONDENSATOREN FÜR INTEGRIERTE HALBLEITERSPEICHER

Title (fr)

PROCEDE DE PRODUCTION DE CONDENSATEURS DE TRANCHEE POUR MEMOIRES INTEGrees A SEMICONDUCTEURS

Publication

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Application

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Abstract (en)

[origin: WO02056369A2] A method for the production of trench capacitors, especially memory cells and at least one selection transistor for integrated semiconductor memories. According to the invention, the trench for the trench capacitor has a lower trench area in which the capacitor is arranged and an upper trench area in which an electrically conducting connection between an electrode of the capacitor to a diffusion area of the selection transistor is disposed. The inventive method reduces the number of process steps for the production of memory cells and enables the production of buried shrouds in the memory capacitors which exhibit the same insulation quality as that which is required for the production of highly integrated memory cells (diameter <300 nm).

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